

# **BeamCal Electronics Status**

FCAL Collaboration Meeting LAL-Orsay, October 5<sup>th</sup>, 2007

Gunther Haller, Dietrich Freytag, Martin Breidenbach and Angel Abusleme



#### **Presentation Outline**

- The BeamCal detector
- BeamCal electronics challenges
- BeamCal electronics operation
- High level design
- Amplifier design
- Filter design
- ADC and memory issues
- Fast feedback design
- Radiation hardness requirements
- Tentative design schedule
- People



#### The BeamCal detector

- Mission:
  - To provide feedback for instantaneous luminosity tuning via beamstrahlung pairs
  - To extend the calorimeter hermeticity to the very forward region (low polar angles)



- BeamCal structure
  - 2 end caps ×
  - 30 Silicon Tungsten sandwiched layers per cap ×
  - 1512 channels per layer
  - Total channel count: 90,720
  - At 32 channels per chip, this implies 2836 chips



#### BeamCal electronics challenges

- 32 channels per chip
- Large input signals, up to 40pC
- High occupancy, all data is read out at 10 bits for science purposes; gated reset is necessary
- Low latency output, sum of all channels is read out after each bx at 8 bits for beam diagnosis (fast feedback)
- Dual-gain front-end (50× ratio), for normal operation and physical signals calibration
- Radiation hardness requirements
- Parasitics due to 15-cm wires between detector and chip, detrimental for front-end performance
- Minimum power dissipation
- Prototype in 0.18-μm TSMC CMOS technology



#### BeamCal electronics operation



- Dual-gain front-end electronics: charge amplifier, pulse shaper and T/H circuit
- Successive approximation ADC, one per channel
- Digital memory, 2820 (10 bits + parity) words per channel
- Analog addition of 32 channel outputs for fast feedback; low-latency ADC



#### BeamCal electronics operation

#### Timing diagram: between pulse trains





#### BeamCal electronics operation

#### Timing diagram: between individual pulses



- Pipelined timing
- Exact timing could be mode-dependent



## High level Design

- Behavioral simulations carried out to find:
  - Best architecture
  - Expected performance
  - Expected power consumption
- Conclusions
  - Charge amplifier current: about 300µA
  - Filter design: CR-RC (bandpass)
  - Peaking time: 200ns



#### High level design

Noise simulation, physics calibration mode





## Amplifier design

- Basic charge amplifier a voltage amplifier and capacitive feedback
- Low noise design (input transistor, gm/Id approach)
- NMOS input device
- Two feedback capacitors for different gains
- Switches for mode selection and reset
- 1-V output swing



Stanford Linear Accelerator Center



## Amplifier design

 SPICE output waveforms, normal operation and physics calibration





- Filter domain
  - Continuous time: issues for  $\tau$  calibration
  - Sampled time: precisely adjustable τ
- Filter topology
  - CR-RC: inadequate for gated reset
  - Biquad: perfect for gated reset
- Implementation details
  - Fully differential, switched-capacitor biquad implementation
  - Using SC inverting integrators (backward Euler integration)
  - Filters voltage across feedback capacitor good PSR
  - 100MHz switching frequency does not affect frequency response in band of interest
  - 25MHz switching frequency does affect frequency response and requires an increase in charge amplifier current in order to meet noise specs



Filter output waveforms, behavioral simulation





#### Amplifier and filter spectra





 Differential, continuous-time biquad...





Conversion to SC + reset transistors





• Output waveforms, normal operation and physics calibration





#### ADC and memory issues

- ADC power consumption is lightly dependent on the number of ADCs
  - one channel per ADC is simple in terms of operation
  - many channels per ADC are efficient in terms of area
  - successive approximation ADCs present a balanced tradeoff, could eventually assign a single channel per ADC without a significant increase in area
- Memory choice: analog or digital?
  - Analog memory problems:
    - high droop rate due to switch leakage in TSMC018 (especially after irradiation)
    - radiation-tolerance techniques are not simple nor flexible
  - Digital memory problems:
    - more area
  - Digital memory will be used mainly due to flexibility



#### Fast feedback design

- Each channel's analog signal is extracted at the track-and-hold circuit output
- Analog adder generates the chip fast feedback signal
- A fast (low-latency) ADC is used to produce the digital output





## Radiation hardness requirements

- Chip must be able to tolerate 1Mrad(SiO<sub>2</sub>) total ionizing dose (TID)
- TSMC018 is naturally tolerant to TID, but some sensitive circuits in the chip require additional protection
- This can be done by using mitigation techniques:
  - Enclosed-layout transistors
  - Guard rings
- Consequences in circuit design:
  - Power consumption increases by 2× or more, depending on the circuit
  - Chip area increases by 2.5× in some circuits
- First prototype will not be radiation-tolerant, but will allow to:
  - assess the technology tolerance to radiation
  - detect the most radiation sensitive circuits



#### Tentative design schedule

- April 2007:
- July 2007:
- October 2007:
- ◆ January 2008:
- February 2008:
- March 2008:
- April 2008:
- ◆ July 2008:
- August 2008:
- October 2008:
- ♦ January 2009:

High level design complete Charge amplifier designed Filter designed ADC designed Memory designed Fast feedback designed Bias and supporting circuits Circuit layout complete Verification complete Prototype ready Prototype tests complete



#### People

- Angel Abusleme (PhD student)<sup>2</sup>
- Professor Martin Breidenbach<sup>1</sup>
- Dietrich Freytag<sup>1</sup>
- Gunther Haller<sup>1</sup>
- Professor Bruce Wooley<sup>2</sup>

#### Affiliations

- 1. SLAC
- 2. Department of Electrical Engineering, Stanford University